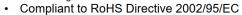


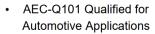
P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
- 60	0.012 at V _{GS} = - 10 V	- 60 ^d			
	0.014 at V _{GS} = - 4.5 V	- 55 ^d			

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested



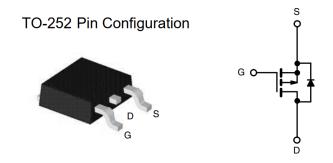




ROHS

APPLICATIONS

- Power Switch
- Load Switch in High Current Applications
- · DC/DC Converters



Top View

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage	V _{DS}	-60	V			
Gate-source voltage	V_{GS}	± 20				
Continuous drain current (T,I = 175 °C)	T _C = 25 °C	_	-60 ^d	A		
Continuous drain current (1) = 175 G)	T _C = 100 °C	l _D	-49			
Pulsed drain current	I _{DM}	-240	^			
Avalanche current	I _{AR}	-55				
Repetitive avalanche energy ^a	L = 0.1 mH	E _{AR}	255	mJ		
Power dissipation	T _C = 25 °C	P _D	196 ^c	· W		
Fower dissipation	T _C = 75 °C	l LD	119 ^{b, c}			
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C		

P-Channel MOSFET

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT		
Junction-to-ambient ^b	t ≤ 10 s	- R _{thJA}	10	14	°C/W	
Junction-to-ambient	Steady state		20	30		
Junction-to-case		R _{thJC}	0.5	0.75		

Notes

- a. Duty cycle ≤ 1%
- b. When mounted on 1" square PCB (FR4 material)
- c. See SOA curve for voltage derating
- d. Package limited



ARAMETER SYMBOL		TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			'	•			
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-	-	V	
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1	-	-3	V	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
		V _{DS} = -48 V, V _{GS} = 0 V	-	-	-1	μΑ	
Zero gate voltage drain current	I _{DSS}	V _{DS} = -48 V, V _{GS} = 0 V, T _J = 125 °C	-	-	-50		
		V _{DS} = -48 V, V _{GS} = 0 V, T _J = 175 °C	-	-	-150		
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ -5 V, V _{GS} = -10 V	-60	-	-	Α	
Drain-source on-state resistance a		$V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	-	0.012	0.015	Ω	
Diain-source on-state resistance	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -15 \text{ A}$	-	0.014	0.022		
Forward transconductance ^a	9 _{fs}	$V_{DS} = -15 \text{ V}, I_D = -20 \text{ A}$	-	64	-	S	
Dynamic ^b							
Input capacitance	C _{iss}		-	10250	-	pF	
Output capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = -30 \text{ V}, f = 1 \text{ MHz}$	-	599	-		
Reverse transfer capacitance	C _{rss}		-	112	-		
Total gate charge ^c	Qg		-	120	-	nC	
Gate-source charge c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	-	69	-		
Gate-drain charge ^c	Q _{gd}		-	38	-		
Turn-on delay time ^c	t _{d(on)}		-	18	-	ns	
Rise time ^c	t _r	$V_{DD} = -30 \text{ V}, R_{L} = 0.6 \Omega$	-	71	-		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -20$ A, $V_{GEN} = -10$ V, $R_G = 6$ Ω	-	125	-		
Fall time ^c	t _f		-	135	-		
Source-Drain Diode Ratings and Ch	aracteristics (T _C = 25 °C) ^b		<u>'</u>			
Continuous current	I _S		-	-	-60	Α	
Pulsed current	I _{SM}		-	-	-240	A	
Forward voltage ^a	V _{SD}	I _F = -20 A, V _{GS} = 0 V	-	0.8	-	V	
Reverse recovery time	t _{rr}	I _F = -20 A, di/dt = 100 A/μs		45	_	ns	

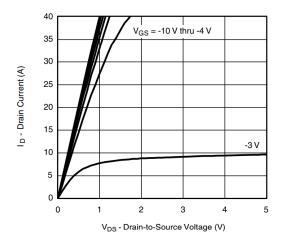
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

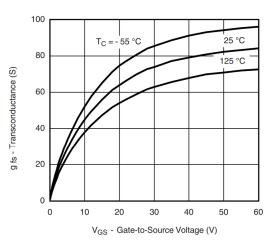
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



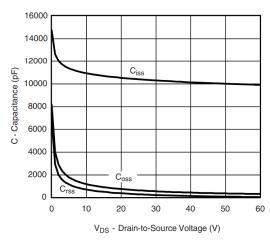
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



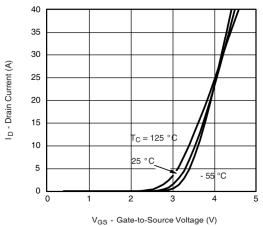
Output Characteristics



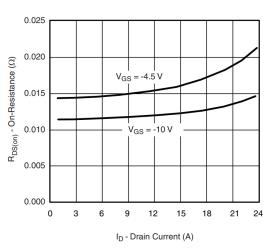
Transconductance



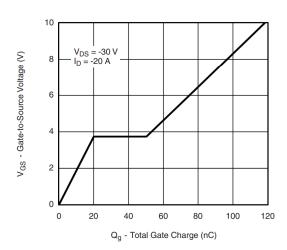
Capacitance



Transfer Characteristics



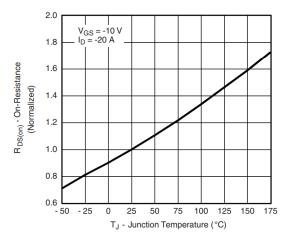
On-Resistance vs. Drain Current



Gate Charge



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

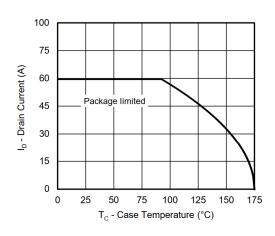


On-Resistance vs. Junction Temperature

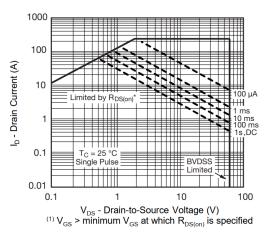
100 T_J = 150 °C T_J = 25 °C T_J = 25 °C T_J = 25 °C V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

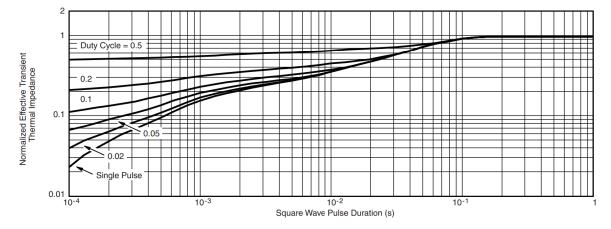
THERMAL RATINGS



Max. Avalanche and Drain Current vs. Case Temperature



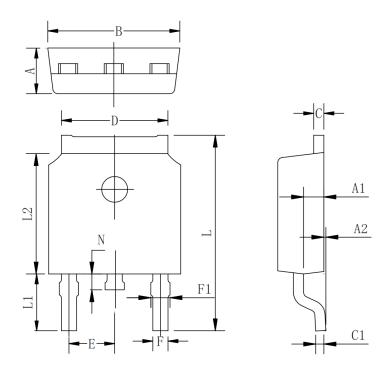
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max		
A	2.10	2.30	2.50		
A1	0.88	1.01	1.16		
A2	0.00	0.15	0.28		
В	6.40	6.60	6.80		
С	0.42	0.50	0.63		
C1	0.42	0.50	0.63		
D	5.08	5.32	5.65		
Е	2.286 TYP				
F	0.63	0.76	0.89		
F1	0.64	0.86	1.08		
L	9.30	9.90	10.80		
L1	2.4	2.8	3.6		
L2	5.90	6.10	6.55		
N	0.57	0.80	1.05		



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